

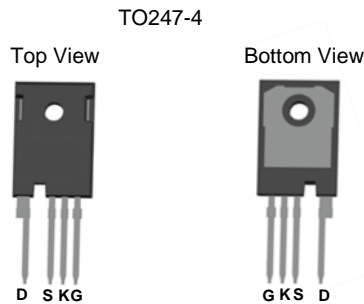
Product Summary

BV_{DSS}	$R_{DS(ON) MAX}$	I_D $T_C = +25^\circ C$
1200V	100m Ω @ $V_{GS} = 15V$	37.2

Description and Applications

This SiC MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Data center and telecom power supplies
- Industrial motor drives
- DC-DC converters
- Solar inverters
- EV battery chargers



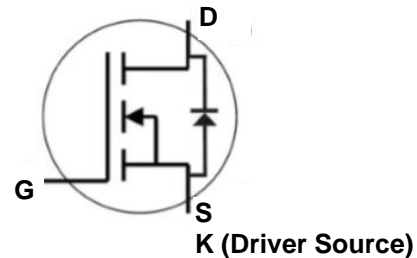
Pin Configuration

Features and Benefits

- Low On-Resistance
- High BV_{DSS} Rating for Power Application
- Low Input Capacitance
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative.**
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

- Package: TO247-4
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Terminal Connections: See Diagram
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ^(e3)
- Weight: 6.6 grams (Approximate)



Internal Schematic

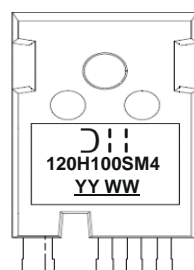
Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Quantity	Carrier
DMWS120H100SM4	TO247-4 (Type WH)	30 Pieces	Tube

- Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

TO247-4 (Type WH)



= Manufacturer's Marking
 120H100SM4 = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 23 = 2023)
 WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	1200	V
Gate-Source Voltage (dynamic)	V _{GSS}	+19/-8	V
Gate-Source Voltage (static)	V _{GSS}	+15/-4	V
Continuous Drain Current (Notes 5, 9)	I _D	T _C = +25°C	37.2
		T _C = +100°C	23.5
Continuous Diode Forward Current (10μs Pulse, Duty Cycle = 1%, Note 5)	I _S	36	A
Pulsed Source Current (Pulse Width t _P Limited by T _{J MAX}) (Note 5)	I _{SM}	87	A
Pulsed Drain Current (Pulse Width t _P Limited by T _{J MAX}) (Note 5)	I _{DM}	87	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	T _C = +25°C	208
		T _C = +100°C	83
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	25.5	°C/W
Thermal Resistance, Junction to Case (Note 5)	R _{θJC}	0.6	
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	1200	—	—	V	V _{GS} = 0V, I _D = 100μA	
Zero Gate Voltage Drain Current	I _{DSS}	—	—	100	μA	V _{DS} = 1200V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	—	—	±200	nA	V _{GS} = +15/-4V, V _{DS} = 0V	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	V _{GS(TH)}	1.7	2.5	3.5	V	V _{DS} = V _{GS} , I _D = 5mA	
Static Drain-Source On-Resistance	R _{DS(ON)}	—	80	100	mΩ	V _{GS} = 15V, I _D = 20A	
Diode Forward Voltage	V _{SD}	—	4.3	—	V	V _{GS} = -4V, I _S = 10A	
Transconductance	g _{fs}	—	3.8	—	S	V _{DS} = 20V, I _D = 20A	
DYNAMIC CHARACTERISTICS (Note 7)							
Input Capacitance	C _{iss}	—	1516	—	pF	V _{GS} = 0V, V _{DS} = 1000V V _{AC} = 25mV, f = 1MHz	
Output Capacitance	C _{oss}	—	55	—			
Reverse Transfer Capacitance	C _{rss}	—	4.16	—			
Coss Stored Energy	E _{oss}	—	35.2	—	μJ	V _{GS} = -4V/+15V, V _{DS} = 800V, R _g = 0Ω, I _D = 20A, L = 156μH	
Turn-On Switching Energy (Body Diode FWD)	E _{on}	—	538	—	μJ		
Turn-Off Switching Energy (Body Diode FWD)	E _{off}	—	79	—	μJ	V _{GS} = -4V/+15V, V _{DS} = 800V, I _D = 20A	
Gate Resistance	R _g	—	8.26	—	Ω		
Total Gate Charge	Q _g	—	52	—	nC	V _{GS} = -4V/+15V, V _{DS} = 800V, I _D = 20A	
Gate-Source Charge	Q _{gs}	—	16	—			
Gate-Drain Charge	Q _{gd}	—	18	—			
Turn-On Delay Time	t _{D(ON)}	—	10.42	—	ns	V _{GS} = -4V/+15V, V _{DD} = 800V, R _g = 0Ω, I _D = 20A, Inductive Load	
Turn-On Rise Time	t _r	—	20.67	—			
Turn-Off Delay Time	t _{D(OFF)}	—	15.05	—			
Turn-Off Fall Time	t _f	—	5.03	—			
Body Diode Reverse Recovery Time	t _{RR}	—	9.88	—	ns	V _{GS} = -4V, V _{DS} = 800V, I _F = 20A, di/dt = 3600A/μs	
Body Diode Reverse Recovery Charge	Q _{RR}	—	98.45	—			nC
Body Diode Reverse Recovery Current	I _{RRM}	—	19.94	—			A

- Notes:
- Device mounted on an infinite heatsink.
 - Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
 - Guaranteed by design. Not subject to production testing.
 - Short duration pulse test used to minimize self-heating effect.
 - Drain current limited by maximum junction temperature.

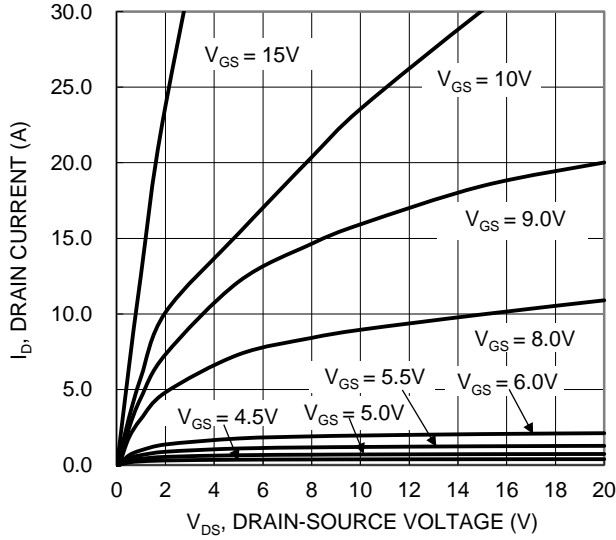


Figure 1. Typical Output Characteristic

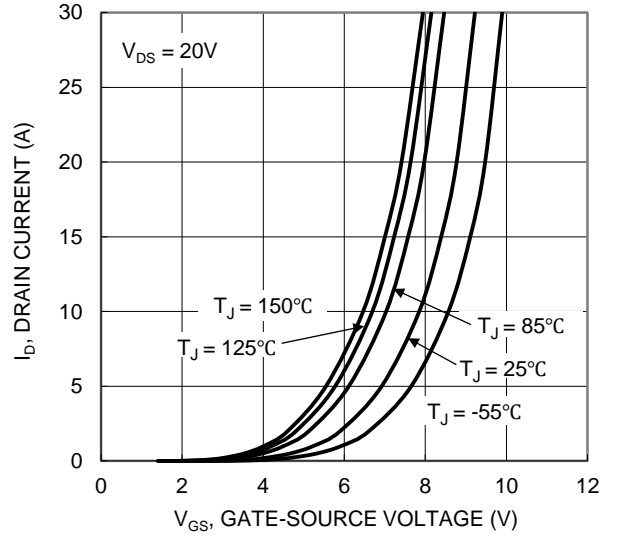


Figure 2. Typical Transfer Characteristic

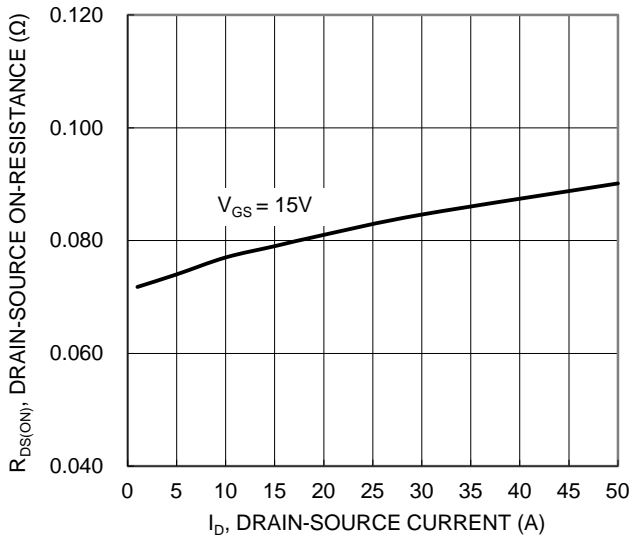


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

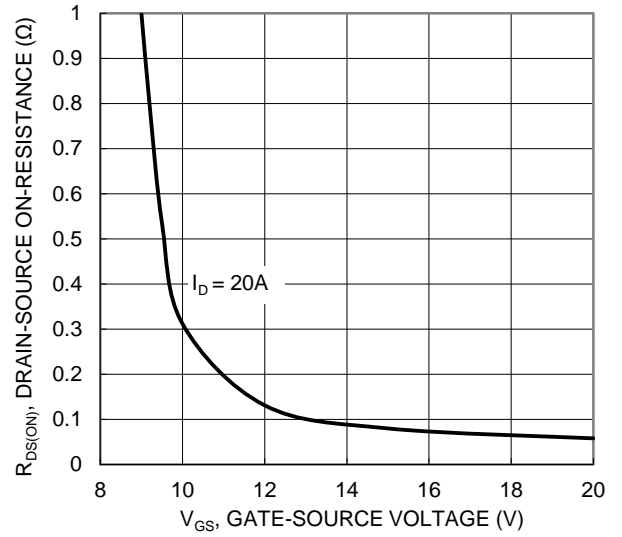


Figure 4. Typical Transfer Characteristic

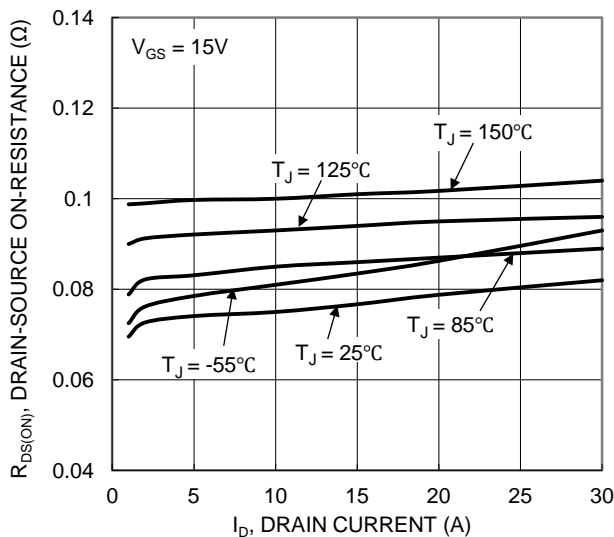


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

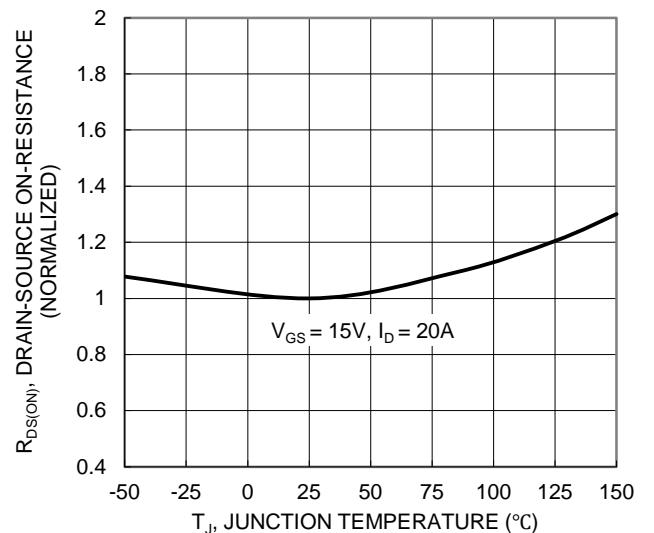


Figure 6. On-Resistance Variation with Junction Temperature

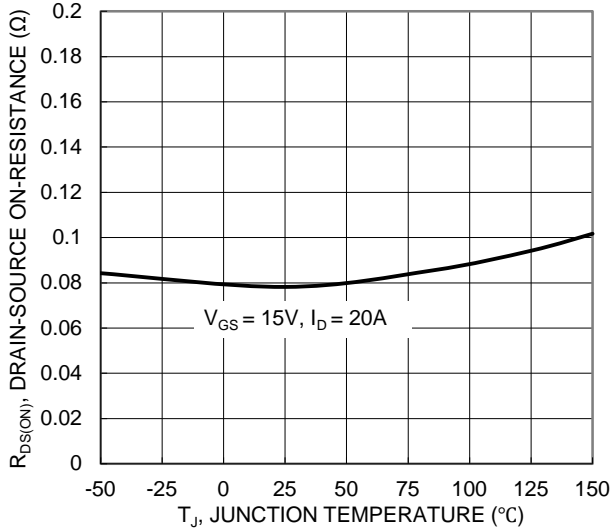


Figure 7. On-Resistance Variation with Junction Temperature

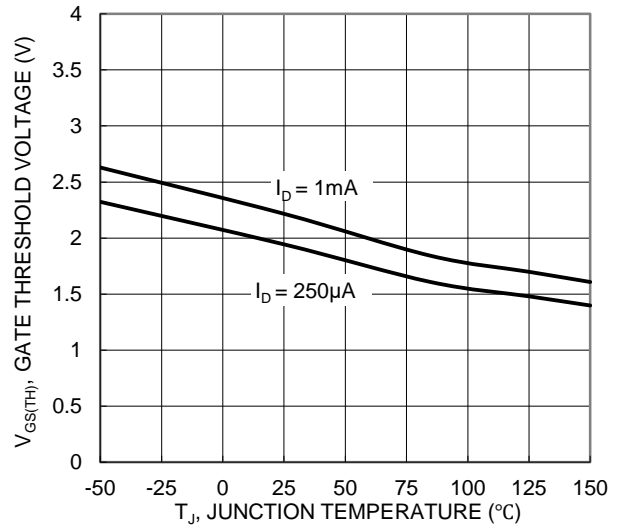


Figure 8. Gate Threshold Variation vs. Junction Temperature

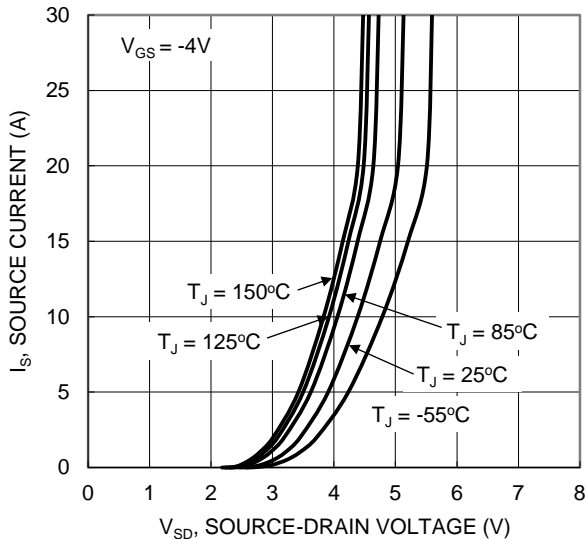


Figure 9. Diode Forward Voltage vs. Current

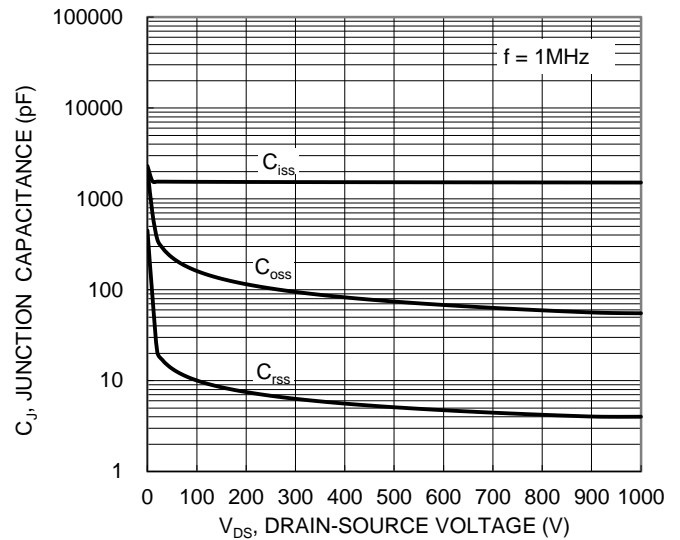


Figure 10. Typical Junction Capacitance

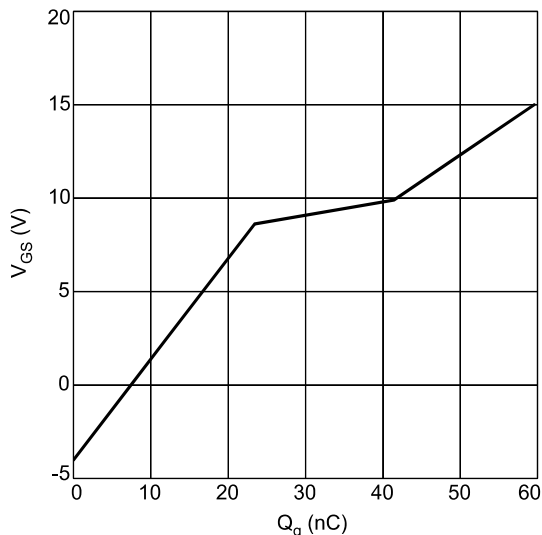


Figure 11. Gate Charge

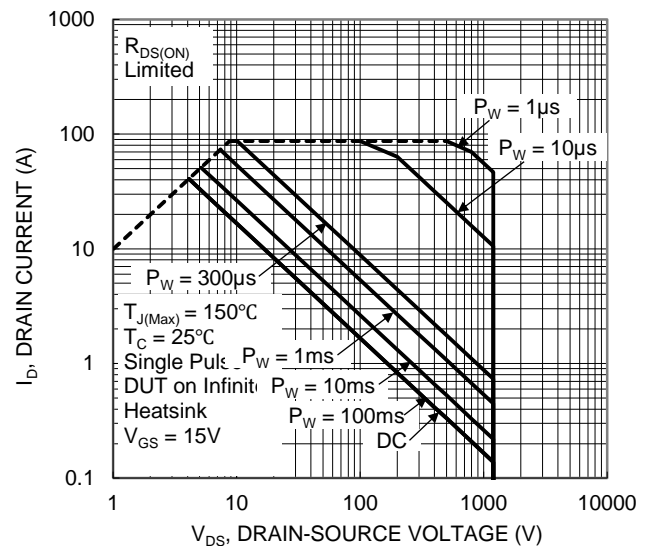


Figure 12. SOA, Safe Operation Area

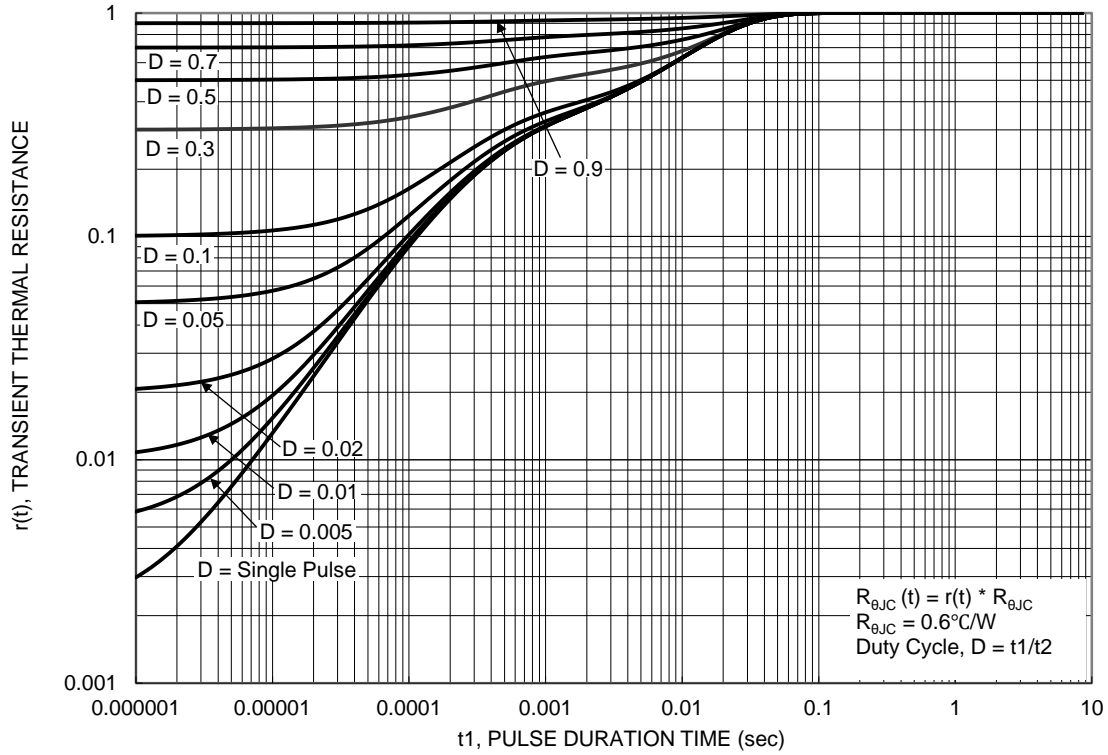
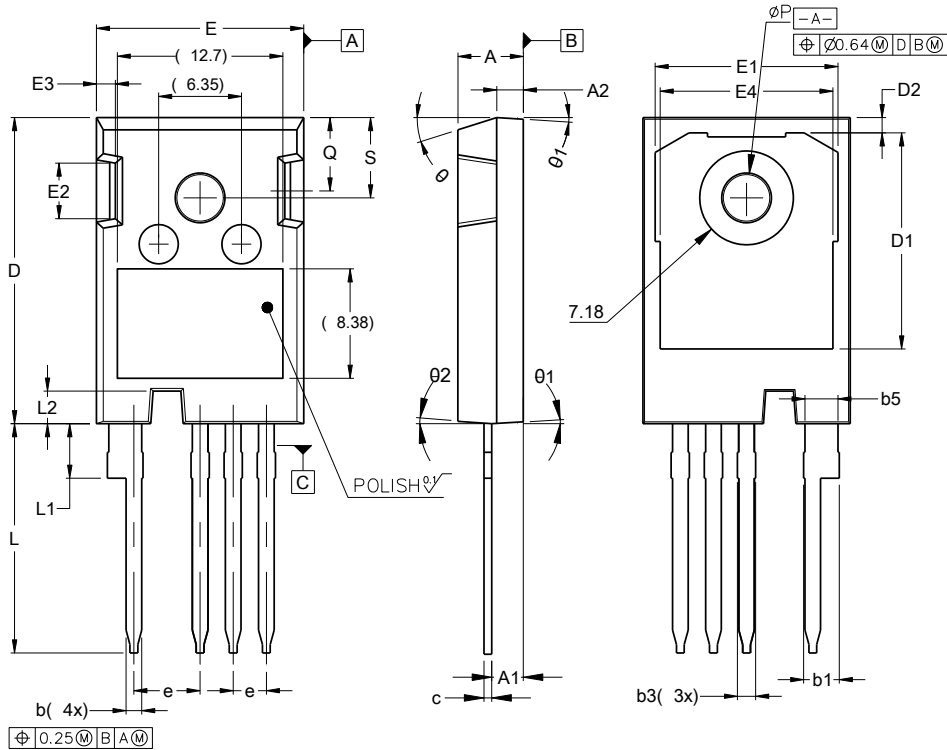


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

TO247-4 (Type WH)



TO247-4 (Type WH)		
Dim	Min	Max
A	4.83	5.21
A1	2.29	2.54
A2	1.91	2.16
b	1.07	1.33
b1	2.39	2.94
b3	1.07	1.60
b5	2.39	2.69
c	0.55	0.68
D	23.30	23.60
D1	16.25	17.65
D2	0.95	1.25
E	15.75	16.30
E1	13.10	14.15
E2	3.68	5.10
E3	1.00	1.90
E4	12.38	13.43
e	2.54 BSC	
e1	5.08 BSC	
L	17.31	17.82
L1	3.97	4.37
L2	2.35	2.65
ØP	3.51	3.65
Q	5.49	6.00
S	6.04	6.30
θ	17.5° REF	
θ1	3.5° REF	
θ2	4° REF	
All Dimensions in mm		

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